

MOSFETs Silicon N-Channel MOS (U-MOSVII-H)

# **TPCA8055-H**

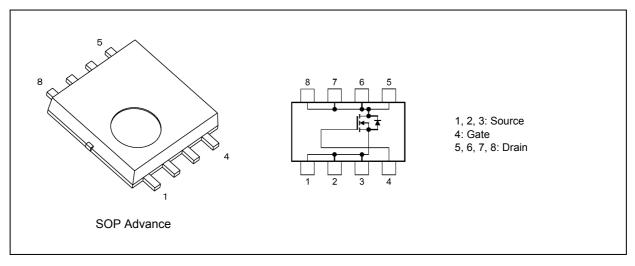
#### 1. Applications

- · High-Efficiency DC-DC Converters
- · Notebook PCs
- · Mobile Handsets

#### 2. Features

- (1) Small, thin package
- (2) High-speed switching
- (3) Small gate charge:  $Q_{SW} = 21 \text{ nC (typ.)}$
- (4) Low drain-source on-resistance:  $R_{DS(ON)} = 1.9 \text{ m}\Omega$  (typ.) ( $V_{GS} = 4.5 \text{ V}$ )
- (5) Low leakage current:  $I_{DSS} = 10 \mu A \text{ (max) (V}_{DS} = 30 \text{ V)}$
- (6) Enhancement mode:  $V_{th} = 1.3 \text{ to } 2.3 \text{ V } (V_{DS} = 10 \text{ V}, I_D = 1.0 \text{ mA})$

### 3. Packaging and Internal Circuit





#### 4. Absolute Maximum Ratings (Note) (Ta = 25°C unless otherwise specified)

Character	ristics		Symbol	Rating	Unit
Drain-source voltage			V <sub>DSS</sub>	30	V
Gate-source voltage			V <sub>GSS</sub>	±20	1
Drain current (DC)		(Note 1)	I <sub>D</sub>	56	Α
Drain current (pulsed)		(Note 1)	I <sub>DP</sub>	168	
Power dissipation	(T <sub>c</sub> = 25°C)		P <sub>D</sub>	70	W
Power dissipation	(t = 10 s)	(Note 2)	P <sub>D</sub>	2.8	W
Power dissipation	(t = 10 s)	(Note 3)	P <sub>D</sub>	1.6	W
Single-pulse avalanche energy		(Note 4)	E <sub>AS</sub>	407	mJ
Avalanche current			I <sub>AR</sub>	56	Α
Channel temperature			T <sub>ch</sub>	150	°C
Storage temperature			T <sub>stg</sub>	-55 to 150	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

#### 5. Thermal Characteristics

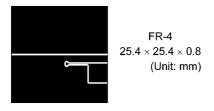
Characteris	stics		Symbol	Max	Unit
Channel-to-case thermal resistance	(T <sub>c</sub> = 25°C)		R <sub>th(ch-c)</sub>	1.78	°C/W
Channel-to-ambient thermal resistance	(t = 10 s)	(Note 2)	R <sub>th(ch-a)</sub>	44.6	°C/W
Channel-to-ambient thermal resistance	(t = 10 s)	(Note 3)	R <sub>th(ch-a)</sub>	78.1	°C/W

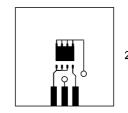
Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: Device mounted on a glass-epoxy board (a), Figure 5.1

Note 3: Device mounted on a glass-epoxy board (b), Figure 5.2

Note 4:  $V_{DD}$  = 24 V,  $T_{ch}$  = 25°C (initial), L = 0.1 mH,  $R_G$  = 1  $\Omega$ ,  $I_{AR}$  = 56 A





 $\begin{aligned} & \text{FR-4} \\ 25.4 \times 25.4 \times 0.8 \\ & \text{(Unit: mm)} \end{aligned}$ 

Fig. 5.1 Device Mounted on a Glass-Epoxy Board (a)

Fig. 5.2 Device Mounted on a Glass-Epoxy Board (b)

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.



#### 6. Electrical Characteristics

### 6.1. Static Characteristics (T<sub>a</sub> = 25°C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I <sub>GSS</sub>	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$	_	_	±0.1	μА
Drain cut-off current	I <sub>DSS</sub>	V <sub>DS</sub> = 30 V, V <sub>GS</sub> = 0 V	_	_	10	
Drain-source breakdown voltage	V <sub>(BR)DSS</sub>	I <sub>D</sub> = 10 mA, V <sub>GS</sub> = 0 V	30	_	_	٧
	V <sub>(BR)DSX</sub>	I <sub>D</sub> = 10 mA, V <sub>GS</sub> = -20 V	15	_		
Gate threshold voltage	$V_{th}$	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 1.0 mA	1.3	_	2.3	
Drain-source on-resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 28 A	_	1.9	2.3	mΩ
		V <sub>GS</sub> = 10 V, I <sub>D</sub> = 28 A	_	1.5	1.9	

### 6.2. Dynamic Characteristics (T<sub>a</sub> = 25°C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C <sub>iss</sub>	V <sub>DS</sub> = 10 V, V <sub>GS</sub> = 0 V, f = 1 MHz	-	6400	7700	pF
Reverse transfer capacitance	C <sub>rss</sub>		_	360	550	
Output capacitance	C <sub>oss</sub>		1	1200		
Gate resistance	r <sub>g</sub>	V <sub>DS</sub> = 10 V, V <sub>GS</sub> = 0 V, f = 5 MHz	_	1.4	2.1	Ω
Switching time (rise time)	t <sub>r</sub>	See Figure 6.2.1.	1	5.7		ns
Switching time (turn-on time)	t <sub>on</sub>			16		
Switching time (fall time)	t <sub>f</sub>		_	11		
Switching time (turn-off time)	t <sub>off</sub>		_	73	_	

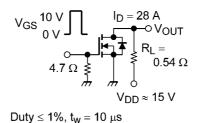


Fig. 6.2.1 Switching Time Test Circuit

# 6.3. Gate Charge Characteristics ( $T_a = 25^{\circ}$ C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus	$Q_g$	$V_{DD} \approx 24 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 56 \text{ A}$	_	91		nC
gate-drain)		$V_{DD} \approx 24 \text{ V}, V_{GS} = 5 \text{ V}, I_{D} = 56 \text{ A}$		47		
Gate-source charge 1	Q <sub>gs1</sub>	$V_{DD} \approx 24 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 56 \text{ A}$		20		
Gate-drain charge	$Q_{gd}$		_	12	_	
Gate switch charge	$Q_{SW}$		_	21	_	

### 6.4. Source-Drain Characteristics (T<sub>a</sub> = 25°C unless otherwise specified)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Reverse drain current (pulsed)	(Note 5)	I <sub>DRP</sub>	_	_		168	Α
Diode forward voltage	·	$V_{DSF}$	I <sub>DR</sub> = 56 A, V <sub>GS</sub> = 0 V	_		-1.2	V

Note 5: Ensure that the channel temperature does not exceed 150°C.



# 7. Marking

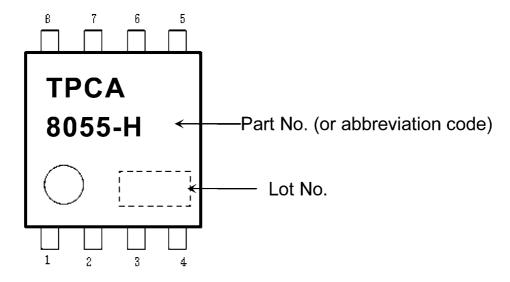


Fig. 7.1 Marking

Rev.2.0

### 8. Characteristics Curves (Note)

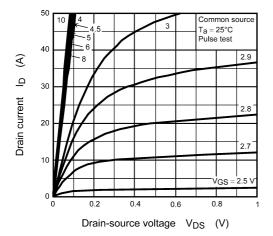


Fig. 8.1  $I_D - V_{DS}$ 

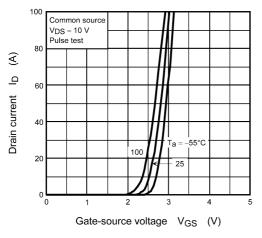


Fig. 8.3 I<sub>D</sub> - V<sub>GS</sub>

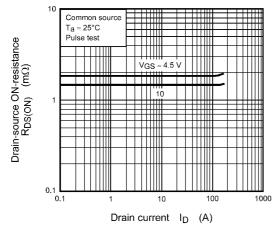


Fig. 8.5 R<sub>DS(ON)</sub> - I<sub>D</sub>

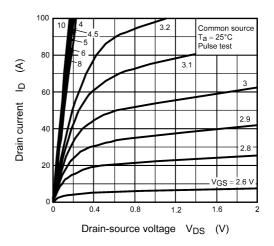


Fig. 8.2  $I_D - V_{DS}$ 

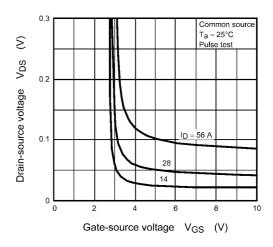


Fig. 8.4 V<sub>DS</sub> - V<sub>GS</sub>

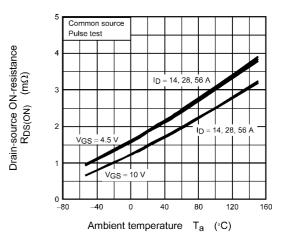


Fig. 8.6 R<sub>DS(ON)</sub> - T<sub>a</sub>

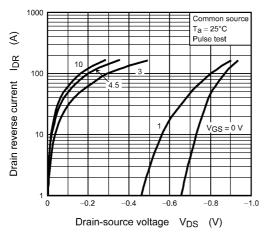


Fig. 8.7 IDR - VDS

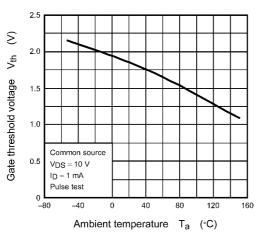


Fig. 8.9 V<sub>th</sub> - T<sub>a</sub>

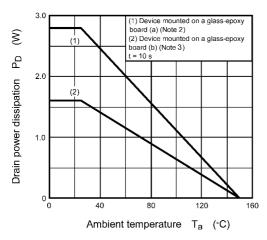


Fig. 8.11 P<sub>D</sub> - T<sub>a</sub> (Guaranteed Maximum)

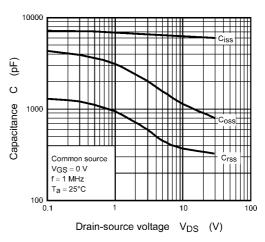


Fig. 8.8 Capacitance - V<sub>DS</sub>

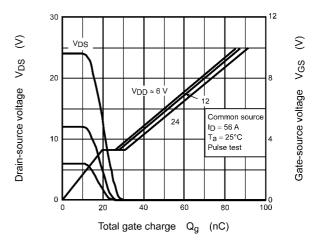


Fig. 8.10 Dynamic Input/Output Characteristics

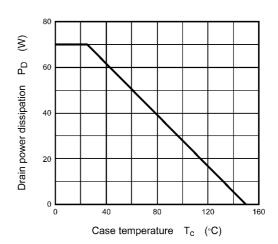


Fig. 8.12 P<sub>D</sub> - T<sub>c</sub> (Guaranteed Maximum)

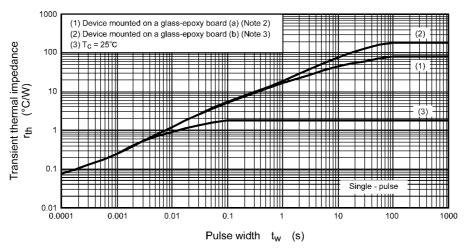


Fig. 8.13 r<sub>th</sub> - t<sub>w</sub> (Guaranteed Maximum)

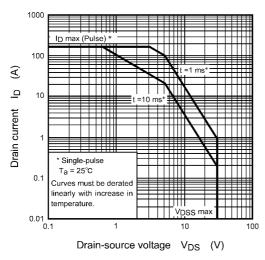


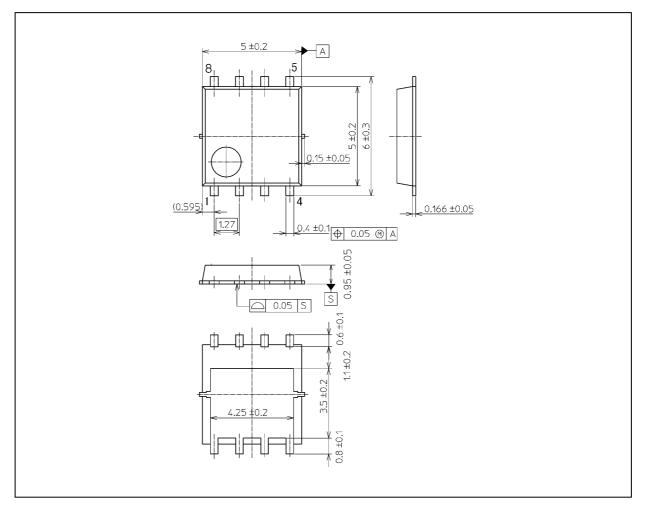
Fig. 8.14 Safe Operating Area (Guaranteed Maximum)

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



### **Package Dimensions**

Unit: mm



Weight: 0.069 g (typ.)

Packa	ge Name(s)
TOSHIBA: 2-5Q1S	
Nickname: SOP Advance	



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